Dual 2-input NAND gate Rev. 3 — 27 March 2013

#### **General description** 1.

The 74AHC2G00; 74AHCT2G00 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

#### **Features and benefits** 2.

- Symmetrical output impedance
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101C exceeds 1000 V
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

#### **Ordering information** 3.

#### **Ordering information** Table 1.

Type number	Package									
	Temperature range	Name	Description	Version						
74AHC2G00DP	–40 °C to +125 °C	TSSOP8								
74AHCT2G00DP			width 3 mm; lead length 0.5 mm							
74AHC2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads;	SOT765-1						
74AHCT2G00DC			body width 2.3 mm							
74AHC2G00GD	–40 °C to +125 °C	XSON8								
74AHCT2G00GD			8 terminals; body $3 \times 2 \times 0.5$ mm							



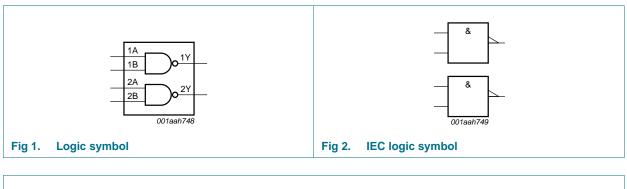
**Dual 2-input NAND gate** 

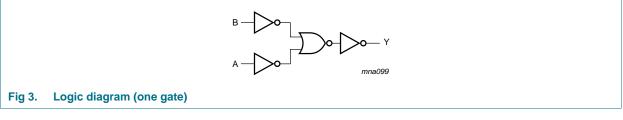
### 4. Marking

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AHC2G00DP	A00
74AHCT2G00DP	C00
74AHC2G00DC	A00
74AHCT2G00DC	C00
74AHC2G00GD	A00
74AHCT2G00GD	C00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram

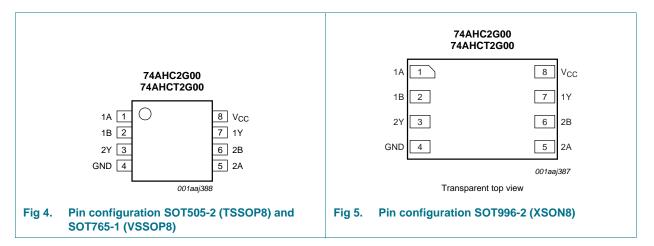




**Dual 2-input NAND gate** 

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

Table 4.	Function table <sup>[1]</sup>		
Input			Output
nA		nB	nY
L		L	Н
L		Н	Н
Н		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	<u>[1]</u> –20	-	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
l <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}}$ + 0.5 V	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
I <sub>GND</sub>	ground current		-75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	bol Parameter Conditions		74	4AHC2G	00	74	Unit		
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

### **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G00									
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
inp	input voltage	$V_{CC} = 3.0 V$	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V

74AHC\_AHCT2G00

Product data sheet

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**Dual 2-input NAND gate** 

Symbol	Parameter	Conditions		25 °C		-40 °C t	to +85 °C	-40 °C t	to +125 °C	Un
			Min	Тур	Max	Min	Мах	Min	Max	
/ <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
√ <sub>ОН</sub>	OH HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -50 \ \mu A; \ V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O}$ = -50 $\mu$ A; $V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
√ <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
	I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V	
I	input leakage current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
СС	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	10	-	40	μA
Cı	input capacitance		-	1.5	10	-	10	-	10	pF
74АНСТ	2G00									
√ <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
√ <sub>ОН</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = –50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		l <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
1	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
сс	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	1.0	-	10	-	40	μ
VI <sub>CC</sub>	additional supply current	per input pin; $V_I = 3.4 V$ ; other inputs at $V_{CC}$ or GND; $I_O = 0 A$ ; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	m
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

## Table 7.Static characteristics ... continuedVoltages are referenced to GND (ground = 0 V).

Product data sheet

**Dual 2-input NAND gate** 

## **11. Dynamic characteristics**

### Table 8. Dynamic characteristics

GND = 0 V; for test circuit see <u>Figure 7</u>.

Symbol	Parameter	eter Conditions		25 °C			–40 °C	to +85 °C	<b>−40 °C</b>	40 °C to +125 °C		
				Min	Тур	Max	Min	Max	Min	Max	1	
74AHC2	G00							1	1			
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	[1]									
	delay	$V_{CC}$ = 3.0 V to 3.6 V	[2]									
		C <sub>L</sub> = 15 pF		-	4.5	7.9	1.0	9.5	1.0	10.5	ns	
		C <sub>L</sub> = 50 pF		-	6.5	11.4	1.0	13.0	1.0	14.5	ns	
		$V_{CC}$ = 4.5 V to 5.5 V	[3]									
		C <sub>L</sub> = 15 pF		-	3.5	5.5	1.0	6.5	1.0	7.0	ns	
		C <sub>L</sub> = 50 pF		-	4.9	7.5	1.0	8.5	1.0	9.5	ns	
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	17	-	-	-	-	-	pF	
74AHCT	2G00											
t <sub>pd</sub>	propagation	nA, nB to nY; see Figure 6	[1]									
	delay	$V_{CC}$ = 4.5 V to 5.5 V	[3]									
		C <sub>L</sub> = 15 pF		1.0	3.6	6.2	1.0	7.1	1.0	8.0	ns	
		C <sub>L</sub> = 50 pF		1.0	5.0	7.9	1.0	9.0	1.0	10.0	ns	
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	18	-	-	-	-	-	pF	

[2] Typical values are measured at  $V_{CC}$  = 3.3 V.

[3] Typical values are measured at  $V_{CC} = 5.0$  V.

 $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

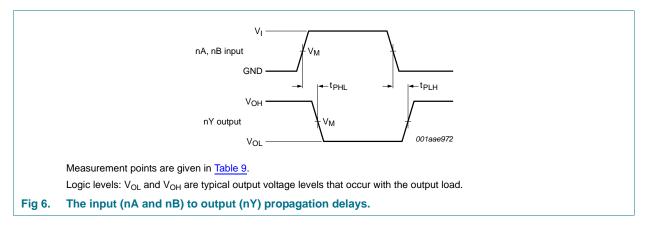
N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

74AHC\_AHCT2G00

**Dual 2-input NAND gate** 

## 12. Waveforms



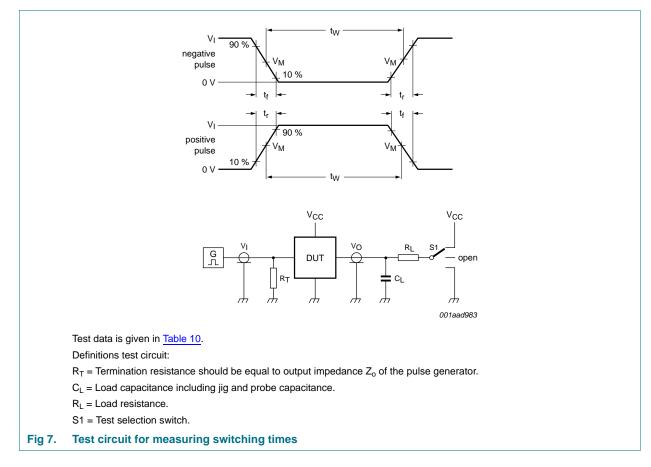
#### Table 9.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC2G00	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74AHCT2G00	1.5 V	0.5V <sub>CC</sub>

### **NXP Semiconductors**

# 74AHC2G00; 74AHCT2G00

### **Dual 2-input NAND gate**

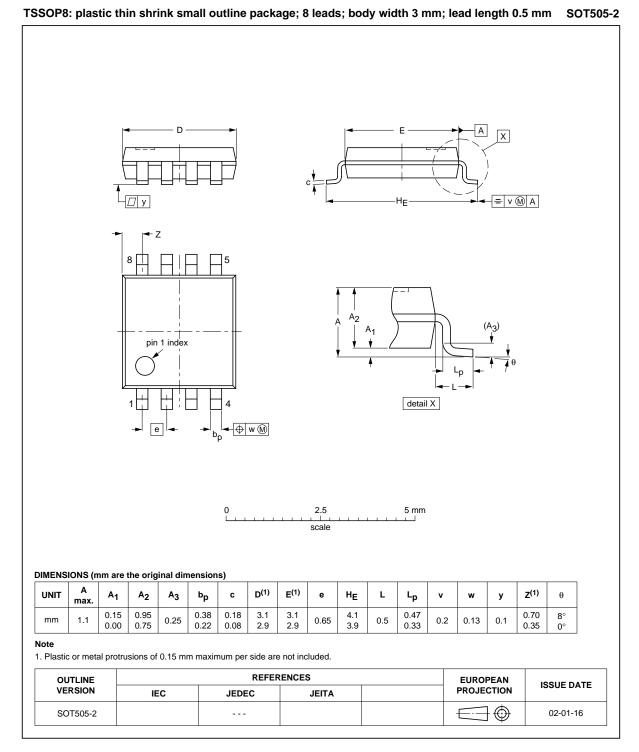


#### Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>
74AHC2G00	V <sub>CC</sub>	≤ 3 ns	15 pF, 50 pF	1 kΩ	open
74AHCT2G00	3 V	$\leq$ 3 ns	15 pF, 50 pF	1 kΩ	open

**Dual 2-input NAND gate** 

## 13. Package outline

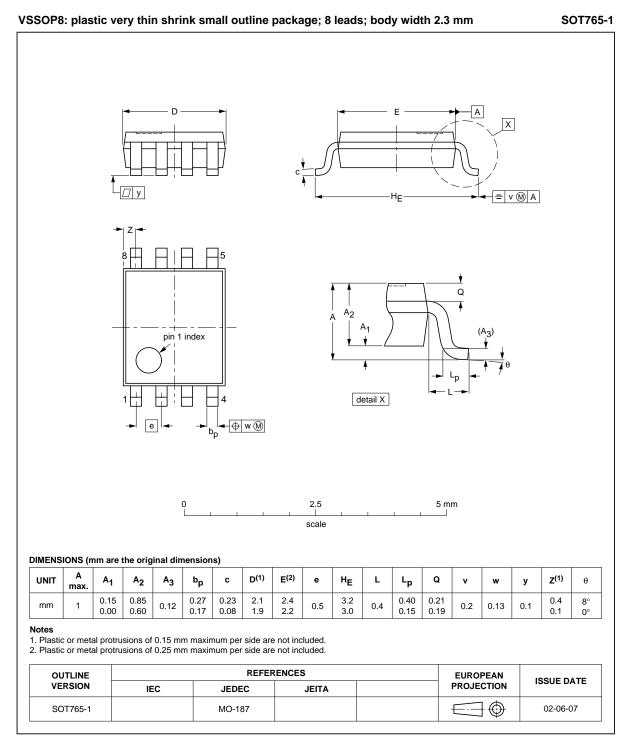


#### Fig 8. Package outline SOT505-2 (TSSOP8)

74AHC\_AHCT2G00

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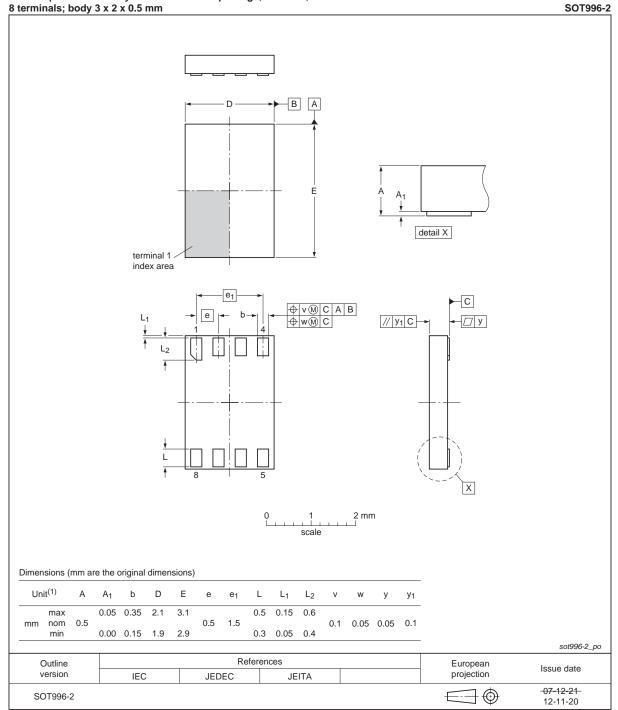
**Dual 2-input NAND gate** 



#### Fig 9. Package outline SOT765-1 (VSSOP8)

74AHC\_AHCT2G00 Product data sheet

**Dual 2-input NAND gate** 



XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

Fig 10. Package outline SOT996-2 (XSON8)

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Product data sheet	Rev. 3 — 27 March 2013	11 of 15

**Dual 2-input NAND gate** 

## 14. Abbreviations

AcronymDescriptionCDMCharged Device ModelCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic Discharge	Abbreviations		
CMOSComplementary Metal-Oxide SemiconductorDUTDevice Under Test			
DUT Device Under Test			
ESD ElectroStatic Discharge			
HBM Human Body Model			
MM Machine Model			
TTL Transistor-Transistor Logic			

## **15. Revision history**

Table 12. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G00 v.3	20130327	Product data sheet	-	74AHC_AHCT2G00 v.2
Modifications:	<ul> <li>For type nun XSON8.</li> </ul>	nbers 74AHC2G00GD and 74	AHCT2G00GD XSO	N8U has changed to
74AHC_AHCT2G00 v.2	20090112	Product data sheet	-	74AHC_AHCT2G00 v.1
74AHC_AHCT2G00 v.1	20040101	Product specification	-	-

### 16. Legal information

### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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74AHC\_AHCT2G00

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**Dual 2-input NAND gate** 

### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1 6.2	Pinning         3           Pin description         3
7	Functional description 3
8	Limiting values
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 6
12	Waveforms 7
13	Package outline
14	Abbreviations 12
15	Revision history 12
16	Legal information 13
16.1	Data sheet status 13
16.2	Definitions 13
16.3	Disclaimers
16.4	Trademarks 14
17	Contact information 14
18	Contents 15

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